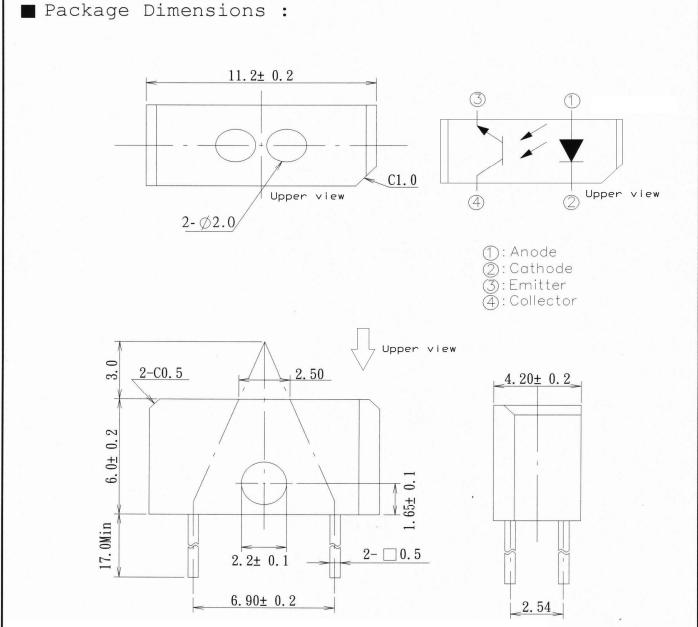
Schematic modified by RWTH Aachen University for Teaching Purposes



EVERLIGHT ELECTRONICS CO, LTD.

Device Number: DRX-904-101 REV: 1.0 MODEL NO: ITR9904 Ecn: Page: 1/8 ■ Package Dimensions :



Office: NO 25, Lane. 76, Chung Yang Rd., Sec. 3, Tucheng, Taipei 236, Taiwan, R.O.C.

1

TEL: 886-2-2267-2000,2267-9936(22Lines)

FAX: 886-2-2267-6189

http://www.everlight.com



Device Number: DRX-904-101 REV: 1.0

MODEL NO: <u>ITR9904</u> Ecn:______ Page:<u>2/8</u>

Description

The **ITR9904** consists of an infrared emitting diode and an NPN silicon phototransistor, encased oblique angle (45°) on converging optical axis in a black thermoplastic housing. The phototransistor receives radiation from the IRED only. This is the normal situation. For additional component information, please refer to **IR1254-R8** and **PT1254-6B**.

Features

ITR:

- Fast response time
- High analytic
- Cut-off visible wavelength $\lambda p=980$ nm
- High sensitivity

■Applications

- Copier
- Scanner
- Non-contact Switching
- For Direct PC Board



Device Number: DRX-904-101 REV: 1.0

MODEL NO: <u>ITR9904</u> <u>Ecn:</u> <u>Page:3/8</u>

Absolute Maximum Ratings (Ta=25 $^{\circ}$ C)

Parameter		Symbol	Ratings	Unit
	Power Dissipation	Pd	100	mW
Input	Reverse Voltage	V_R	5	V
	Forward Current	$\mathtt{I}_{\mathtt{F}}$	50	mA
	Peak Forward Current (*1)	${ t I}_{ t FP}$	1.0	А
	Collector Power Dissipation	PC	75	mW
Output	Collector Current	Ι _C	20	mA
	Collector-Emitter Voltage	$V_{ ext{CEO}}$	30	V
	Emitter-Collector Voltage	V_{ECO}	5	V
Operating Temperature		Topr	-25~+85	$^{\circ}\!\mathbb{C}$
Storage Temperature		Tstg	-40~+85	$^{\circ}\mathbb{C}$
Solderi	ng Temperature (*2)	Tsol	260	$^{\circ}\!\mathbb{C}$

(*1) tw=100 μ sec., Duty cycle=1% (*2) t=5 Sec

\blacksquare Electrical Characteristics (Ta=25 $^{\circ}$ C)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions
Input	Forward Voltage	$V_{\rm F1}$	ı	1.2	1.5	V	I _F =20mA
		$V_{\rm F2}$	_	1.4	1.85	V	$I_F=100$ mA
		$V_{\rm F3}$	-	2.6	4.0	V	I _F =1A
	Reverse Current	ΙR	ı	-	10	μΑ	V _R =5 V
	Peak Wavelength	λP	ı	940	-	nm	_
	View Angle	2€1/2	-	35	-	Deg	$I_F=20mA$
	Dark Current	Iceo	-	_	100	nA	V_{CE} =20V
							Ee=0mW/cm ²
Output	C-E Saturation	VcE(sat)	-	-	0.4	V	$I_{C}=2\mathrm{mA}$
	Voltage						$I_B = 0.1$ mA
		Ic(ON)A	100	_	300		
Collector	Current	Ic(on)B	200	-	600	μА	$V_{CE}=5V$
	_	Ic(ON)C	400	1	1200		I _F =20mA
Speed	Rise time	t _R	_	15	_	$\mu \sec$	Vce=2v
	Fall time	$t_{\mathbb{F}}$	_	15	-	$\mu\mathrm{sec}$	$I_{\text{C}} = 1\text{mA}$
							Rl=1K Ω



Device Number: <a href="https://documents.org/levises/bases/

■ Typical Characteristics For IR

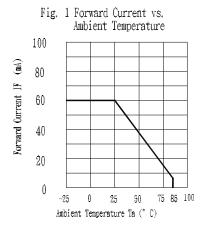


Fig. 3 Peak Emission Wavelength vs. Ambient Temperature

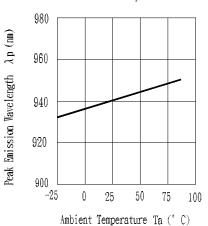
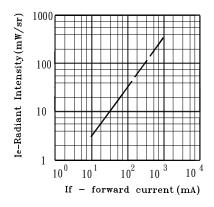


Fig. 5 Relative Intensity vs. Forward Current



Relative Radiant Intensity (%)

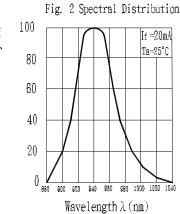


Fig. 4 Forward Current vs.
Forward Voltage

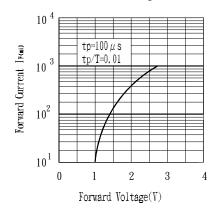
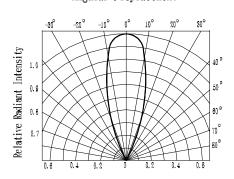


Fig. 6 Relative Radiant Intensity vs.
Angular Displacement





Device Number: DRX-904-101 REV: 1.0

MODEL NO: <u>ITR9904</u> Ecn:_____ Page:<u>5/8</u>

■ Typical Characteristics For PT

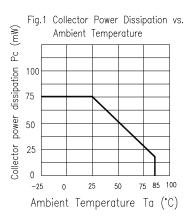


Fig. 3 Relative Collector Current vs. Ambient Temperature

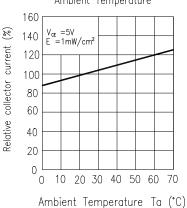
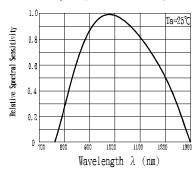


Fig.5 Spectral Sensitivity



Wavelength λ (nm)

Fig.2 Collector Dark Current vs. Ambient Temperature

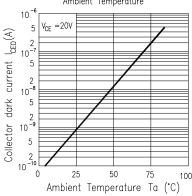


Fig.4 Collector Current vs. Irradiance

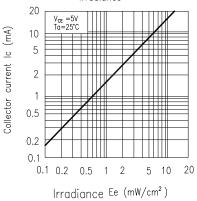
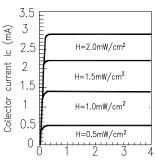


Fig.6 Collector Current vs.
Collector—emitter Voltage



Collector-emitter Voltage V ce (V)



Device Number: DRX-904-101 REV: 1.0

MODEL NO: <u>ITR9904</u> Ecn:______ Page: <u>6/8</u>

■ Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

	level: 90% LTPD: 10%		
Items	Purpose & Condition	Failure Judgement	Samples(n)
		Criteria	Defect (c)
Temperature	Evaluates product's ability to		n=22,c=0
Cycle	withstand exposure to high	I _R ≧U x 2	
	temperature, low temperature,	$Ic(on) \leq L \times 0.8$	
	and temperature variation between	$V_F \ge U \times 1.2$	
	two limit temperature.		
	Standard test Condition:		
	85°C ~25°C ~−55°C ~25°C		
	\downarrow \downarrow \downarrow	U: Upper	
	30min 5min 30min 5min	specification	
	50 cycle	limit	
Thermal Shoc	k Evaluates product's ability to		$n = 22 \cdot c = 0$
	withstand rapid temperature	L: Lower	
	change Standard test	specification limit	
	Condition: $85^{\circ}C \sim -55^{\circ}C$	TIMILC	
	5min(10sec)5min		
	50cycle		
High	Evaluates product's ability to		n =22, c=0
Storage	withstand prolonged storage		
	at high temperature Standard		
	test Condition:		
	Temperature : 100 $^{\circ}\mathrm{C}$		
	Time : 1000hrs		
Low	Evaluates product's ability to		n = 22, c = 0
Storage	withstand prolonged storage		
	at low temperature Standard		
	test Condition:		
	Temperature : -55 $^{\circ}$ C		
	Time: 1000hrs		



Device Number: $\underline{DRX-904-101}$ REV: $\underline{1.0}$

Items	Purpose & Condition	Failure Judgement	Samples(n)
1001110		Criteria	——————————————————————————————————————
		Criteria	Defective(c)
Operating Life	Evaluates product's endurance		$n = 22 \cdot c = 0$
	to prolonged electrical or	$I_R \ge U \times 2$	
	temperature stresses. Standard	$Ic(on) \leq L \times 0.8$	
	test Condition:	$V_F \ge U \times 1.2$	
	$V_{CE}=5V$		
	$I_F=20mA$		
	Time : 1000hrs		
High Temperature	Evaluates product's ability to	U:Upper	n = 22 , c = 0
	withstand prolonged storage	specification	
High Humidity	at high temperature and high	limit	
	humidity. Standard test	T . T	
	Condition:	L:Lower	
	Temperature: 85℃	specification	
	Relative humidity:85%	limit	
	Time : 1000hrs		
Soldering Heat	Evaluates product's ability to		n = 22 , c = 0
	withstand soldering heat		
	Standard test conditions		
	Solder temperature : $260\pm5^{\circ}$ C		
	Solder time : 10 seconds		

Supplement

(1) Chip

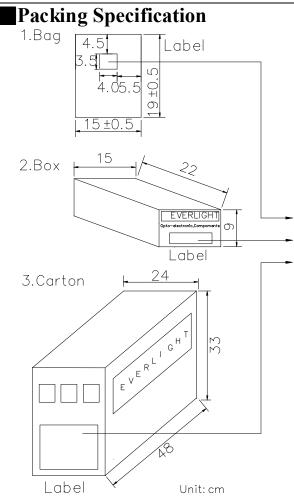
Туре	Material	Peak Wavelength
IR	GaAlAs	940nm
PT	Silicon	980nm

(2) Material

Туре	Lead frame	Wire	Package	Holder
ITR	SPCC	Gold	Ероху	NORYL



Device Number: DRX-904-101 REV: 1.0



CPN: Customer's product number

P/N: Product number

QTY: Packing quantity

CAT: Ranks

HUE: Peak wavelength

REF: Reference

LOT NO: Lot number

MADE IN TAIWAN: Production place

Packing Quantity Specification

1.200Pcs/1Bag

2.6Bags/1Box

3.10Boxes/1Carton